Ref #	Hits	Search Query	DBs	Default Operat or	Plural s	Time Stamp
L1	50877	((cvd (chemical same vapor same deposit\$3) ALD (atomic same layer same deposit\$3) pulse plasma)).CLM.	US-PGPU B	OR	ON	2005/12/05 11:36
L2	679	((substrate wafer) and (reactor chamber) and (vapor and (reactant precursor))).CLM.	US-PGPU B	OR	ON	2005/12/05 11:37
<b>L4</b>	48092	(pulse cycle).CLM.	US-PGPU B	OR	ON	2005/12/05 11:37
L10	30418	(PSG (phosphosilicate and glass) (phosphorous and dop\$3 ( ("Si" "O.sub.2"))) (silicon same (oxide dioxide))).CLM.	US-PGPU B	OR	ON	2005/12/05 11:38
<b>L12</b>	50964	((cvd chemisorb\$3 (chemical same vapor same deposit\$3) ALD (atomic same layer same deposit\$3) pulse plasma)). CLM.	US-PGPU B	OR	ON	2005/12/05 11:40
L13	50964	L1 L12	US-PGPU B	OR	ON	2005/12/05 11:40
L14	49	L2 and L4 and L10	US-PGPU B	OR	ON	2005/12/05 11:40

Ref #	Hits	Search Query	DBs	Default Operat or	Plural s	Time Stamp
L2	36581	ALD (atomic near5 layer near5 deposit\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/12/05 11:09
L3	56	L2 and (phosphorus near5 (silicon near5 (oxide dioxide)))	US-PGPU B; USPAT; USOCR	OR	ON	2005/12/05 11:09
L4	56	L3 and phosphorus	US-PGPU B; USPAT; USOCR	OR	ON	2005/12/05 11:09
L5	14192	PSG (phosphours near5 doped near5 (silicon near5 (dioxide oxide)))	US-PGPU B; USPAT; USOCR	OR	ON	2005/12/05 11:11
L6	14192	PSG (phosphours near5 dop\$3 near5 (silicon near5 (dioxide oxide)))	US-PGPU B; USPAT; USOCR	OR	ON	2005/12/05 11:11
L7	14192	L5 L6	US-PGPU B; USPAT; USOCR	OR	ON	2005/12/05 11:11
<b>L8</b>	372	L7 and (ALD (atomic near5 layer near5 deposit\$3))	US-PGPU B; USPAT; USOCR	OR	ON	2005/12/05 11:11
L9	3012	pulse near5 deposit\$3	US-PGPU B; USPAT; USOCR	OR	ON	2005/12/05 11:12
L10	565	L9 and (silicon near5 oxide)	US-PGPU B; USPAT; USOCR	OR	ON	2005/12/05 11:12
L11	87	("Si" near5 "O" near5 "CH" near5 "OH")	US-PGPU B; USPAT; USOCR	OR	ON	2005/12/05 11:12
L15	3379	chemisorb\$3	US-PGPU B; USPAT; USOCR	OR	ON	2005/12/05 11:15
L16	3047	L15 and (silicon (oxide dioxide))	US-PGPU B; USPAT; USOCR	OR	ON	2005/12/05 11:15
L17	548	L16 and phosphorus	US-PGPU B; USPAT; USOCR	OR	ON	2005/12/05 11:15

L18	248	L17 and (pulse cvd ALD (atomic near5 layer near5 deposit\$3) plasma (chemical near5 vapor near5 deposit\$3))	US-PGPU B; USPAT; USOCR	OR	ON	2005/12/05 11:15
L19	431	chemisorb\$3	EPO; JPO; DERWENT	OR	ON	2005/12/05 11:17
L20	137	L19 and (silicon (oxide dioxide))	IBM_TDB EPO; JPO; DERWENT	OR	ON	2005/12/05 11:17
L21	3	L20 and phosphorus	IBM_TDB EPO; JPO; DERWENT	OR	ON	2005/12/05 11:17
			iBM_TDB			
L22	240390	(plasma cvd ALD (atomic near5 layer near5 deposit\$3) (chemical near5 vapor near5 deposit\$3))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/12/05 11:18
L23	2081	L22 and (BPSG PSG (borophosphosilicate near5 glass) (dop\$3 near5 silicon near5 (oxide dioxide)))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/12/05 11:18
L24	38	L23 and ( phosphorus near5 dop\$3 near5 silicon near5 (oxide dioxide))	EPO; JPO; DERWENT	OR	ON	2005/12/05 11:18
			, IBM_TDB			